ALPHANUMERIC INDEX — CROSS-REFERENCE

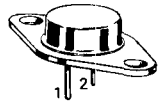
The following table represents an index and cross-reference guide for all low-frequency power transistors which are either manufactured directly by Motorola or for which Motorola manufactures a suitable equivalent. Where the Motorola part number differs from the industry part number, the Motorola device is a "form, fit and function" replacement for the industry type number — however, subtle differences in characteristics and/or specifications may exist.

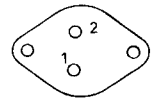
1

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
1SI10A-100		MJ16018	3-782
2N1487		2N5877	3-120
2N1488		2N5878	3-120
2N1489		2N5877	3-120
2N1490		2N5878	3-120
2N1702		2N5877	3-120
2N3016		2N5337	3-97
2N3021		2N3789	3-56
2N3022		2N3789	3-56
2N3023		2N3789	3-56
2N3024		2N3791	3-56
2N3025		2N3791	3-56
2N3026		2N3791	3-56
2N3054	2N3054		3-2
2N3054A	2N3054A		3-2
2N3055	2N3055		3-6
2N3055A	2N3055A		3-9
2N3055H		2N3055A	3-9
2N3055JAN		2N5302JAN	3-93
2N3055SD		2N3055A	3-9
2N3055UB		2N3055A	3-9
2N3076		2N6249	3-164
2N3079		2N6308	3-181
2N3080		2N6543	3-215
2N3171		2N3789	3-56
2N3172		2N3789	3-56
2N3173		2N3790	3-56
2N3174		MJ15016	3-9
2N3183		2N3789	3-56
2N3184		2N3789	3-56
2N3185		2N3790	3-56
2N3186		MJ15016	3-9
2N3195		2N3789	3-56
2N3196		2N3790	3-56
2N3198		MJ15016	3-9
2N3202		2N3719	3-32
2N3203		2N3720	3-32
2N3204		2N6303	3-32
2N3232		2N5877	3-120
2N3233		2N5882	3-123
2N3234		2N5760	3-116
2N3235		2N3055	3-6
2N3236		2N5882	3-123
2N3237		2N5302	3-93
2N3238		2N5882	3-123
2N3239		2N5882	3-123
2N3240		2N5882	3-123
2N3419		2N5336	3-97
2N3420		2N5336	3-97
2N3421		2N5336	3-97

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
2N3441	2N3441		3-13
2N3442	2N3442		3-15
2N3445	2N3447		3-18
2N3446	2N3448		3-18
2N3447	2N3447		3-18
2N3448	2N3448		3-18
2N3583	2N3583		3-20
2N3584	2N3584		3-20
2N3585	2N3585		3-20
2N3667		2N5881	3-123
2N3713		2N5881	3-123
2N3714	2N3714		3-26
2N3715	2N3715		3-26
2N3715JAN	2N3715JAN		3-26
2N3715JTX	2N3715JTX		3-26
2N3715JTXV	2N3715JTXV		3-26
2N3716	2N3716		3-26
2N3716JAN	2N3716JAN		3-26
2N3716JTX	2N3716JTX		3-26
2N3716JTXV	2N3716JTXV		3-26
2N3719	2N3719		3-32
2N3720	2N3720		3-32
2N3738	2N3738		3-37
2N3739	2N3739		3-37
2N3739JAN	2N3739JAN		3-37
2N3739JTX	2N3739JTX		3-37
2N3739JTXV	2N3739JTXV		3-37
2N3740	2N3740		3-41
2N3740A		2N3740	3-41
2N3740JAN	2N3740JAN		3-41
2N3740JTX	2N3740JTX		3-41
2N3740JTXV	2N3740JTXV		3-41
2N3741	2N3741		3-41
2N3741A	2N3741A		3-41
2N3741JAN	2N3741JAN		3-41
2N3741JTX	2N3741JTX		3-41
2N3741JTXV	2N3741JTXV		3-41
2N3766	2N3766		3-44
2N3766JAN	2N3766JAN		3-44
2N3766JTX	2N3766JTX		3-44
2N3766JTXV	2N3766JTXV		3-44
2N3767	2N3767		3-44
2N3767JAN	2N3767JAN		3-44
2N3767JTX	2N3767JTX		3-44
2N3767JTXV	2N3767JTXV		3-44
2N3771	2N3771		3-48
2N3772	2N3772		3-48
2N3773	2N3773		3-52
2N3788		2N6543	3-215
2N3789	2N3789		3-56

TABLE 3 — METAL TO-213 (Formerly TO-66)





STYLE 1:
PIN 1. BASE
2. EMITTER
CASE. COLLECTOR

CASE 80-02 (TO-213AA)

I_CCont Amps Max	$V_{CEO(sus)}$ Volts Min	Device Type NPN	Device Type PNP	h_{FE} Min/Max	@ I_C Amp	Resistive Switching t_s μs Max	Resistive Switching t_f μs Max	Resistive Switching @ I_C Amp	f_T MHz Min	P_D (Case) Watts @ 25°C
1	80	2N4912		20/100	0.5	0.6 typ	0.3 typ	0.5	3	25
	175	2N3583	2N6420	40/200	0.5	2 typ	0.23 typ	0.5	10	35
	225	2N3738		40/200	0.1	3 typ	0.3 typ	0.1	10	20
	300	2N3739		40/200	0.1	3 typ	0.3 typ	0.1	10	20
2	225		2N6211	10/100	1	2.5	0.6	1	20	35
	250	2N3584	2N6421	25/100	1	4	3	1	10	35
	300		2N6212	10/100	1	2.5	0.6	1	20	35
		2N3585	2N6422	25/100	1	4	3	1	10	35
		2N4240		30/150	0.75	6	3	0.75	15	35
	350		2N6213	10/100	1	2.5	0.6	1	20	35
3	140	2N3441		25/100	0.5				0.2	25
4	60		2N3740	30/100	0.25	1.3 typ	0.27 typ	0.25	4	25
		2N3054,A		25/100	0.5	1 typ	0.3 typ	0.5	3	75
		2N3766		40/160	0.5	0.9 typ	0.09 typ	0.5	10	20
		2N6294##	2N6296##	750/18k	2	0.9 typ	0.7 typ	2	4#	50
	80		2N3741	30/100	0.25	1.3 typ	0.27 typ	0.25	4	25
		2N3767		40/160	0.5	0.9 typ	0.09 typ	0.5	10	20
		2N6295##	2N6297##	750/18k	2	0.9 typ	0.7 typ	2	4	50
5	80	2N4233A		25/100	1.5	0.5 typ	0.2 typ	1.5	4	75
7	60		2N6317	20/100	2.5	1	0.8	2.5	4	90
	80	2N5428		60/240	2	2	0.2	2	30	40
			2N6318	20/100	2.5	1	0.8	2.5	4	90
	100	2N5429		30/120	2	2	0.2	2	30	40
		2N5430		60/240	2	2	0.2	2	30	40
8	60	2N6300##	2N6298##	750/18k	4	1.5 typ	1.5 typ	4	4#	75
	80	2N6301##	2N6299##	750/18k	4	1.5 typ	1.5 typ	4	4#	75

$|h_{fe}|$ @ 1 MHz, ## Darlington

JAN, JTX, JTXV Available

TABLE 14 — SWITCHMODE POWER TRANSISTORS (continued)

$V_{CEO(sus)}$ Volts Min	I_C Cont Amps Max	V_{CEV} Volts Min	Device Type NPN unless otherwise noted	h_{FE} Min/Max	@ I_C Amp	Resistive Switching t_s μs Max	Resistive Switching t_f μs Max	Resistive Switching @ I_C Amp	f_T MHz Min	P_D (Case) Watts @ 25°C	Case JEDEC/MOT
400	8	850	2N6545★	7/35	5	4	1	5	6		TO-204/1
		800	MJE5742#	200/400	4	8 typ	2 typ	6			TO-220/221A
		800	MJE16080	5 min	8	2	0.5	5		80	TO-220/221A
		850	BUW12	6 min	6	4	0.8	5		125	TO-218/340
		850	BUX84	30 min	0.1	3.5	1.4	1	4	50	TO-220/221A
		700	MJE13007★	6/30	5	3	0.7	5	4		TO-220/221A
		650	MJ13080★	8 min	5	1.5	0.5	5			TO-204/1
		650	MJE16106	6/25	8	2 typ	0.1 typ	5		100	TO-220/221A
		650	MJH16106	6/25	8	2 typ	0.1 typ	5		125	TO-218/340
		450	MJ6503-PNP★	15 min	2	2	0.5	4			TO-204/1
		450	MJE5852-PNP★	15 min	2	2	0.5	4			TO-220/221A
	6	900	BU326A	30 typ	0.6	3.5	1**	2.5	6	90	TO-204/1
		900	BU426A	30 typ	0.6	2 typ	0.5 typ	2.5	6 typ	113	TO-218/340D
	5	850	2N6543★	7/35	3	4	0.8	3	6		TO-204/1
		850	BUW11	6 min	3	4	0.8	3		125	TO-218/340
		650	MJ13070★	8 min	3	1.5	0.5	3			TO-204/1
		650	MJE13070★	8 min	3	1.5	0.5	3			TO-220/221A
	4	700	MJE13005★	6/30	3	3	0.7	3	4		TO-220/221A
	1.5	700	MJE13003★	5/25	1	4	0.7	1	5		TO-225AA/77R
	0.5	400	MJ4647-PNP	20 min	0.5	0.72*		0.05	40		TO-205AD/79
375	6	800	BU326	30 typ	0.6	3.5	1**	2.5	6	90	TO-204/1
		800	BU426	30 typ	0.6	2 typ	0.5 typ	2.5	6 typ	113	TO-218/340D
350	40	450	MJ10022##★	50/600	10	2.5	0.9	20			TO-204/197
	20	450	MJ10000#★	40/400	10	3	1.8	10	10**		TO-204/1
		450	MJ10004##★	40/400	10	1.5	0.5	10	10**		TO-204/1
	15	375	2N6251	6/50	10	3.5	1	10	2.5		TO-204/1
	10	450	MJ10002#★	30/300	5	2.5	1	5	10**		TO-204/1
		450	MJ10006##★	30/300	5	1.5	0.5	5	10**		TO-204/1
		400	MJ13014★	8/20	5	2	0.5	5			TO-204/1
	8	700	2N6308	12/60	3	1.6	0.4	5	5		TO-204/1
		700	MJE5741#	200/400	4	8 typ	2 typ	6			TO-220/221A
		400	MJE5851-PNP	15 min	2	2	0.5	4			TO-220/221A
	2	400	2N6213-PNP	10/100	1	2.5	0.6	1	4		TO-213AA/80
325	30	400	BUV23	8 min	16	1.8	0.4	16	8	250	TO-204/197
	15	400	BUX13	8 min	8	2.5	0.8	8	8	150	TO-204/1
	5	350	2N6235	25/125	1	3.5	0.5	1	20		TO-213AA/80
300	15	650	2N6546★	6/30	10	4	0.7	10	6 to 24		TO-204/1
	12	600	MJE13008★	6/30	8	3	0.7	8	4**		TO-220/221A
	8	600	2N6307	15/75	3	1.6	0.4	3	5		TO-204/1
		600	MJE13006★	6/30	5	3	0.7	5	4		TO-220/221A
		600	MJE5740	200/400	4	8 typ	2 typ	6			TO-220/221A
		350	MJE5850-PNP★	15 min	2	2	0.5	4			TO-220/221A
	5	400	2N6498	10/75	2.5	1.8	0.8	2.5	5		TO-220/221A
	4	600	MJE13004★	6/30	3	3	0.7	3	4		TO-220/221A
	2	500	2N3585	25/100	1	4	3	1	10		TO-213AA/80
		500	2N6422-PNP	25/100	1	4	3	1	10		TO-213AA/80
		350	2N6212-PNP	10/100	1	2.5	0.6	1	4		TO-213AA/80
	1.5	600	MJE13002★	5/25	1	4	0.7	1	5		TO-225AA/77R

★ Designers Data Sheet characterization
Darlington ## Darlington with speed-up diode * t_{off} ** $|h_{fe}|$ @ 1 MHz

(continued)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

NPN
2N3583 thru 2N3585
2N4240
PNP
2N6420 thru 2N6422

COMPLEMENTARY MEDIUM-POWER HIGH VOLTAGE POWER TRANSISTORS

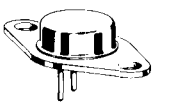
. . . designed for high-speed switching and linear amplifier applications for high-voltage operational amplifiers, switching regulators, converters, inverters, deflection stages and high fidelity amplifiers.

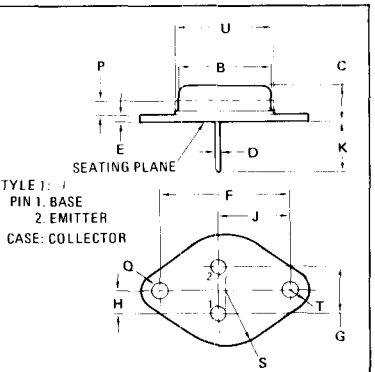
- Collector-Emitter Sustaining Voltage –
  $V_{CEO(sus)}$ = 175 to 300 Vdc @ I_C = 200 mAdc
- Second Breakdown Collector Current –
  $I_{s/b}$ = 350 mAdc @ V_{CE} = 100 Vdc – NPN
  = 150 mAdc @ V_{CE} = 100 Vdc – PNP
- Usable DC Current Gain to 2.0 Adc

1.0 AND 2.0 AMPERE

POWER TRANSISTORS COMPLEMENTARY SILICON

250-500 VOLTS
35 WATTS





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
B	11.94	12.70	0.470	0.500
C	6.35	8.64	0.250	0.340
D	0.71	0.86	0.028	0.034
E	1.27	1.91	0.050	0.075
F	24.33	24.43	0.958	0.962
G	4.83	5.33	0.190	0.210
H	2.41	2.67	0.095	0.105
J	14.48	14.99	0.570	0.590
K	9.14	–	0.360	–
P	–	1.27	–	0.050
Q	3.61	3.86	0.142	0.152
S	–	8.89	–	0.350
T	–	3.68	–	0.145
U	–	15.75	–	0.620

All JEDEC Dimensions and and Notes Apply.

CASE 80-02
TO-213AA
(TO-66)

*MAXIMUM RATINGS

Rating	Symbol	2N3583 2N6420	2N3584 2N6421	2N3585 2N6422	2N4240	Unit
Collector-Emitter Voltage	V_{CEO}	175	250	300	300	Vdc
Collector-Base Voltage	V_{CB}	250	375	500	500	Vdc
Emitter-Base Voltage	V_{EB}	6.0				Vdc
Collector Current – Continuous	I_C	1.0	2.0			Adc
–Peak (1)		5.0	5.0			
Base Current	I_B	1.0				Adc
Total Power Dissipation @ T_C = 25°C,	P_D	35				Watts
Derate above 25°C		0.2				W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5.0	°C/W

*Indicates JEDEC Registered Data

(1) Pulse Test: Pulse Width = 5.0 ms, Duty Cycle ≤ 10%.

3

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	NPN	PNP	Symbol	NPN Min	NPN Max	PNP Min	PNP Max	Unit
***OFF CHARACTERISTICS (1)**								
Collector-Emitter Sustaining Voltage	2N3583	2N6420	$V_{CEO(sus)}$	175	–	175	–	Vdc
(I_C = 200 mAdc, I_B = 0) NPN	2N3584	2N6421		250	–	250	–	
	2N3585	2N6422		300	–	300	–	
(I_C = 50 mAdc, I_B = 0) PNP	2N4240			300	–	300	–	
Collector Cutoff Current			I_{CEO}					mAdc
(V_{CE} = 150 Vdc, I_B = 0)	2N3583	2N6420		–	10	–	10	
	2N3584	2N6421		–	5.0	–	5.0	
	2N3585	2N6422		–	5.0	–	5.0	
	2N4240			–	5.0	–	5.0	
Collector Cutoff Current			I_{CEX}					mAdc
(V_{CE} = 225 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	2N3583	2N6420		–	1.0	–	1.0	
(V_{CE} = 340 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	2N3584	2N6421		–	1.0	–	1.0	
(V_{CE} = 450 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	2N3585	2N6422		–	1.0	–	1.0	
	2N4240			–	2.0	–	2.0	
(V_{CE} = 225 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	2N3583	2N6420		–	3.0	–	3.0	
(V_{CE} = 300 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	2N3584	2N6421		–	3.0	–	3.0	
	2N3585	2N6422		–	3.0	–	3.0	
	2N4240			–	5.0	–	5.0	
Emitter Cutoff Current			I_{EBO}					mAdc
(V_{BE} = 6.0 Vdc, I_C = 0)	2N3583	2N6420		–	5.0	–	5.0	
	2N3584	2N6421		–	0.5	–	0.5	
	2N3585	2N6422		–	0.5	–	0.5	
	2N4240			–	0.5	–	0.5	
ON CHARACTERISTICS (1)								
DC Current Gain	All	All	h_{FE}					–
(I_C = 0.1 Adc, V_{CE} = 10 Vdc)				40	–	40	–	
*(I_C = 0.5 Adc, V_{CE} = 10 Vdc)	2N3583	2N6420		40	200	40	200	
*(I_C = 0.75 Adc, V_{CE} = 2.0 Vdc)	2N4240			10	100	10	100	
(I_C = 0.75 Adc, V_{CE} = 10 Vdc)	2N4240			30	150	30	150	
*(I_C = 1.0 Adc, V_{CE} = 2.0 Vdc)	2N3584	2N6421		8.0	80	8.0	80	
	2N3585	2N6422		8.0	80	8.0	80	
(I_C = 1.0 Adc, V_{CE} = 10 Vdc)	2N3583*	2N6420		10	–	10	–	
	2N3584	2N6421		25	100	25	100	
	2N3585	2N6422		25	100	25	100	
*Collector-Emitter Saturation Voltage			$V_{CE(sat)}$					Vdc
(I_C = 0.75 Adc, I_B = 75 mAdc)	2N4240			–	1.0	–	1.0	
(I_C = 1.0 Adc, I_B = 125 mAdc)	2N3583	2N6420		–	5.0	–	5.0	
	2N3584	2N6421		–	0.75	–	0.75	
	2N3585	2N6422		–	0.75	–	0.75	
*Base-Emitter Saturation Voltage			$V_{BE(sat)}$					Vdc
(I_C = 0.75 Adc, I_B = 75 mAdc)	2N4240			–	1.8	–	1.8	
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N3584	2N6421		–	1.4	–	1.4	
	2N3585	2N6422		–	1.4	–	1.4	
Base-Emitter On Voltage	All	All	$V_{BE(on)}$					Vdc
(I_C = 1.0 Adc, V_{CE} = 10 Vdc)				–	1.4	–	1.4	

*Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

3

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	NPN	PNP	Symbol	NPN Min	NPN Max	PNP Min	PNP Max	Unit
DYNAMIC CHARACTERISTICS								
*Current Gain – Bandwidth Product[1] (I_C = 200 mAdc, V_{CE} = 10 Vdc, f_{test} = 5.0 MHz)	2N3583 2N3584 2N3585 2N4240	2N6420 2N6421 2N6422	f_T	10 15	– –	10 15		MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	All		C_{ob}	–	120	–	120	pF
*Small-Signal Current Gain (I_C = 100 mAdc, V_{CE} = 30 Vdc, f = 1.0 kHz)	2N3583	2N6420	h_{fe}	25	350	25	350	
***SWITCHING CHARACTERISTICS**								
Rise Time (V_{CC} = 200 Vdc, I_C = 1.0 Adc, R_L = 200 Ohms, I_{B1} = 100 mAdc) (V_{CC} = 200 Vdc, I_C = 0.75 Adc, R_L = 267 Ohms, I_{B1} = 75 mAdc)	2N3584 2N3585 2N4240	2N6421 2N6422	t_r	–	3.0 0.5	–	3.0 0.5	μs
Storage Time (V_{CC} = 200 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc) (V_{CC} = 200 Vdc, I_C = 0.75 Adc, I_{B1} = I_{B2} = 75 mAdc)	2N3584 2N3585 2N4240	2N6421 2N6422	t_s	– –	4.0 6.0	– –	4.0 6.0	μs
Fall Time (V_{CC} = 200 Vdc, I_C = 1.0 Adc, I_{B1} = I_{B2} = 100 mAdc) (V_{CC} = 200 Vdc, I_C = 0.75 Adc, I_{B1} = I_{B2} = 75 mAdc)	2N3584 2N3585 2N4240	2N6421 2N6422	t_f	 –	3.0 3.0	– –	3.0 3.0	μs
Second Breakdown Collector Current (V_{CE} = 100 Vdc)	All	All	$I_{s/b}$	350	–	150	–	mAdc

*Indicates JEDEC Registered Data

[1] $f_T = |h_{fe}| \bullet f_{test}$

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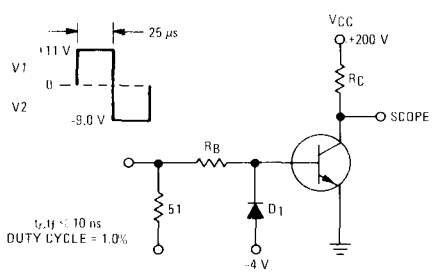
FIGURE 1 – SWITCHING TIME TEST CIRCUIT

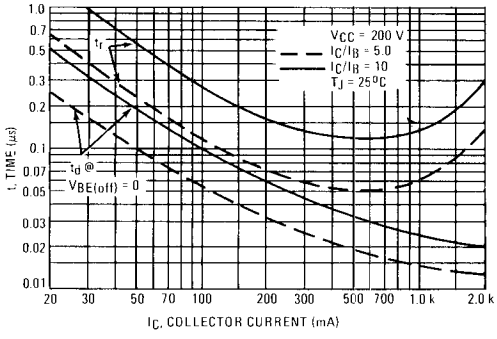


R_B and R_C VARIED TO OBTAIN DESIRED CURRENT LEVELS
D_1 MUST BE FAST RECOVERY TYPE, eg:
MBD5300 USED ABOVE I_B ≈ 100 mA
MSD6100 USED BELOW I_B ≈ 100 mA
FOR t_d and t_r, D1 IS DISCONNECTED AND V_2 = 0.
FOR PNP TEST CIRCUIT, REVERSE DIODE AND VOLTAGE POLARITIES.

NPN
2N3583 thru 2N3585, 2N4240

PNP
2N6420 thru 2N6422

FIGURE 2 – TURN-ON TIME



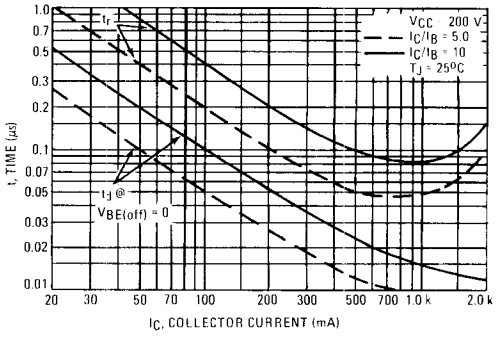
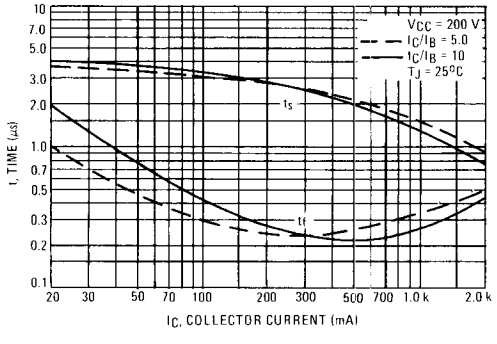


FIGURE 3 – TURN-OFF TIME



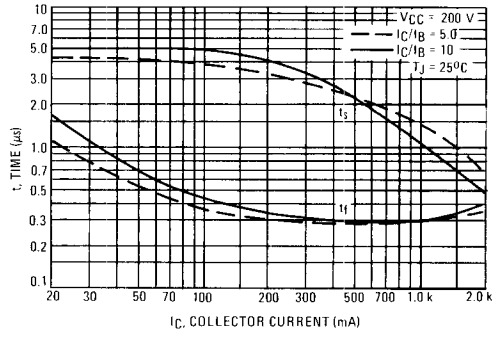


FIGURE 4 – CURRENT-GAIN – BANDWIDTH PRODUCT

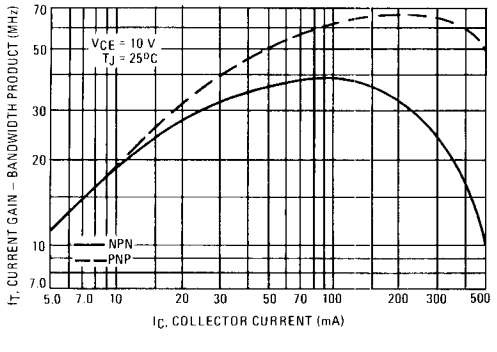


FIGURE 5 – CAPACITANCE

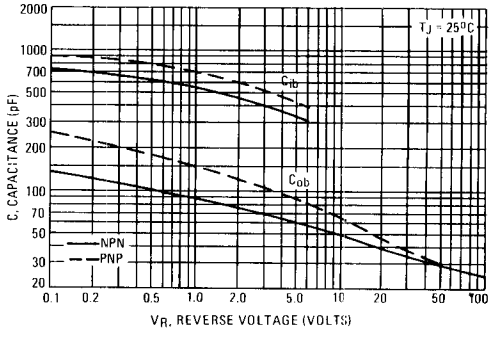


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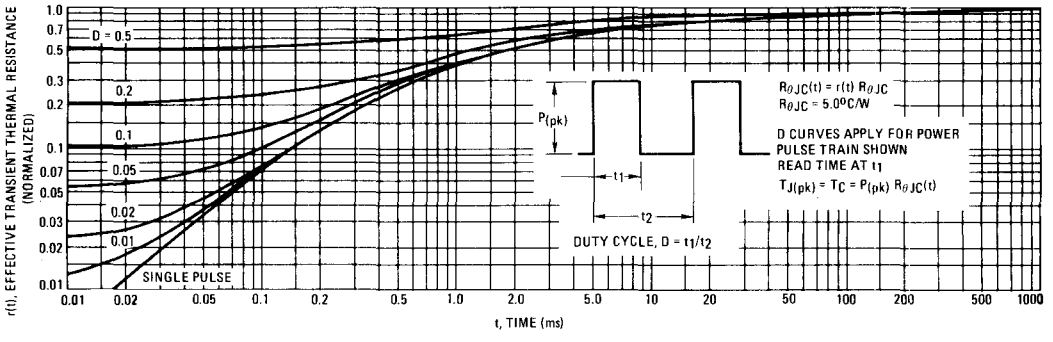
FIGURE 6 – THERMAL RESPONSE



ACTIVE-REGION SAFE OPERATING AREA

FIGURE 7 – 2N3583 thru 2N3585, 2N4240

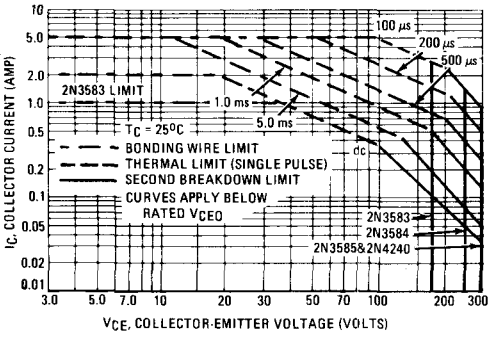


FIGURE 8 — 2N6420 thru 2N6422

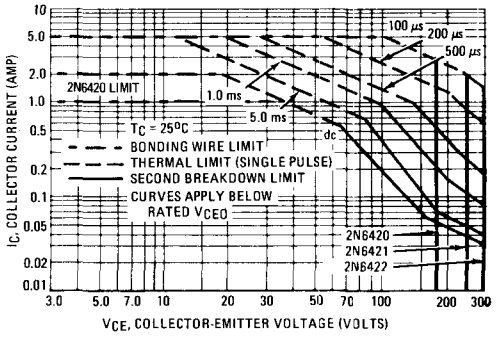
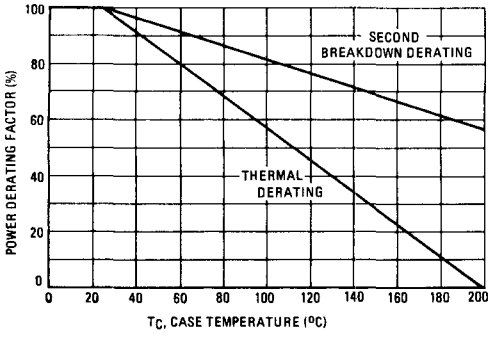


FIGURE 9 – POWER DERATING



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 7 and 8 is based on $T_C = 25^oC$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 9.

$T_{J(pk)}$ may be calculated from the data in Figure 6. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figures 7 and 8 may be found at any case temperature by using the appropriate curve on Figure 9.

NPN
2N3583 thru 2N3585, 2N4240

PNP
2N6420 thru 2N6422

FIGURE 10 – DC CURRENT GAIN

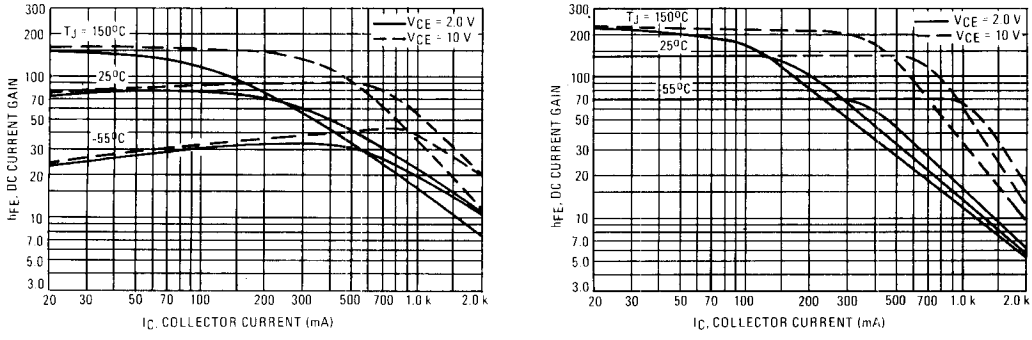


FIGURE 11 – COLLECTOR SATURATION REGION

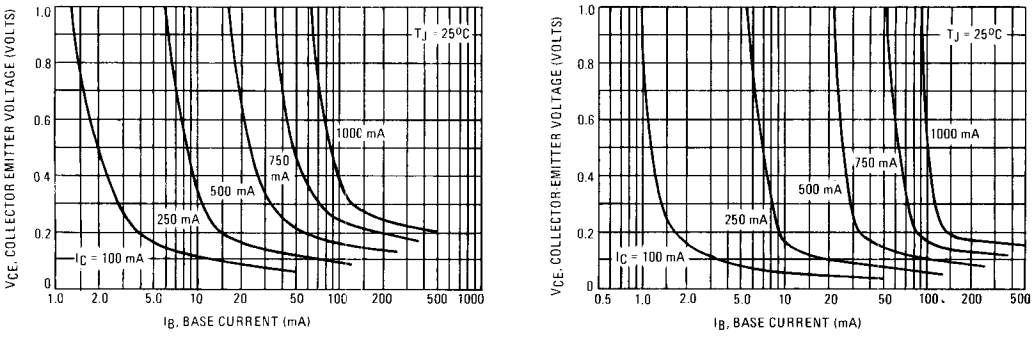
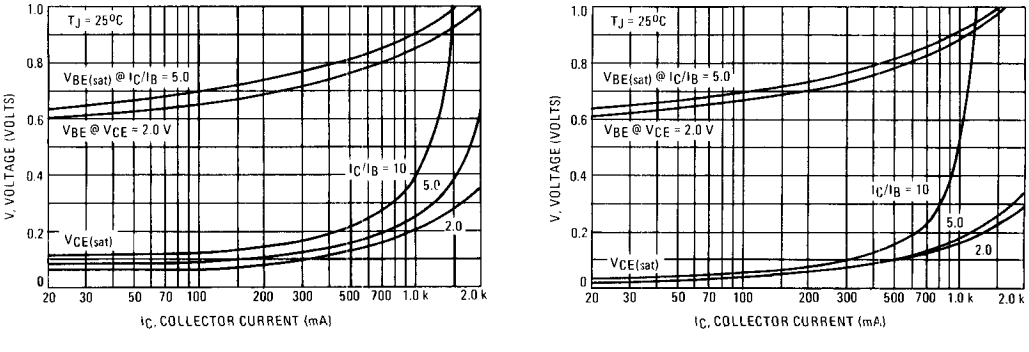


FIGURE 12 – "ON" VOLTAGES



NOTE: DC CURRENT LIMIT FOR 2N3583, 2N6420 is 1.0 Amp.

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